

isc N-Channel Mosfet Transistor

IRF3710

• FEATURES

- Drain Current $-I_D=57A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}= 100V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(\text{on})} = 23m\Omega (\text{Max})$

• DESCRIPTION

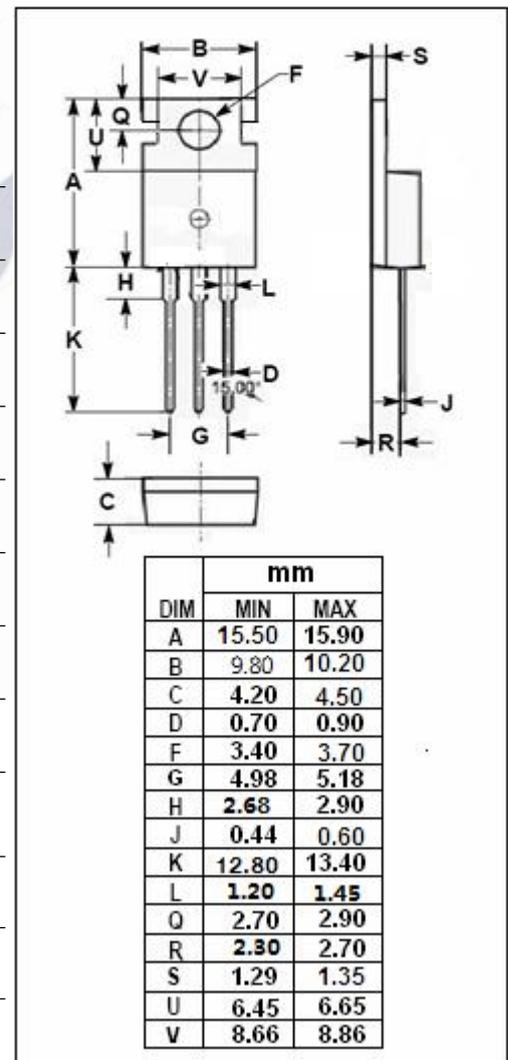
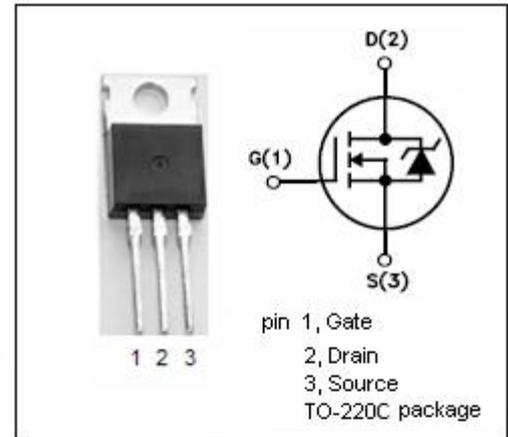
- Designed for high efficiency switch mode power supplies, Power factor correction and electronic lamp ballasts based on half bridge.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	57	A
I_{DM}	Drain Current-Single Plused	230	A
P_D	Total Dissipation @ $T_C=25^{\circ}C$	200	W
T_j	Max. Operating Junction Temperature	-55~175	$^{\circ}C$
T_{stg}	Storage Temperature	-55~175	$^{\circ}C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	0.75	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance,Junction to Ambient	62	$^{\circ}C/W$



isc N-Channel Mosfet Transistor
IRF3710
ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	100		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 0.25mA	2	4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 28A		0.023	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V; V _{GS} =0		25	uA
V _{SD}	Forward On-Voltage	I _S = 28A; V _{GS} =0		1.2	V